NPN Epitaxial Planar Silicon Transistor



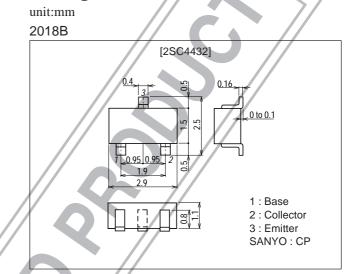
2SC4432

High-Frequency General-Purpose Amplifier Applications

Features

- · High power gain.
- · High cutoff frequency.
- · Small Cob, Cre.
- · Ultrasmall-sized package permitting the 2SC4432applied sets to be made small and slim.

Package Dimensions



Specifications

Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		40	V
Collector-to-Emitter Voltage	VCEO		18	V
Emitter-to-Base Voltage	VEBO		3	V
Collector Current	IC		50	mA
Collector Dissipation	Pc		250	mW
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector Cutoff Current	Ісво	V _{CB} =18V, I _E =0			0.1	μA
Emitter Cutoff Current	ГЕВО	V _{EB} =2V, I _C =0			0.1	μΑ
DC Current Gain	hFE	V _{CE} =10V, I _C =5mA	60*		270*	
Gain-Bandwidth Product	ĺΤ	V _{CE} =10V, I _C =5mA		750		MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		0.7	1.2	pF
Reverse transfer Capacitance	Cre	V _{CB} =10V, f=1MHz		0.45		pF

Marking : RT * : The 2SC4432 is classified by 5mA h_{FE} as follows :

Rank	-3	4	5
^b FE	60 to 120	90 to 180	135 to 270

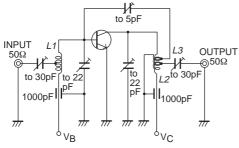
Continued on next page.

- Any and all SANYO products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your SANYO representative nearest you before using any SANYO products described or contained herein in such applications.
- SANYO assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all SANYO products described or contained herein.

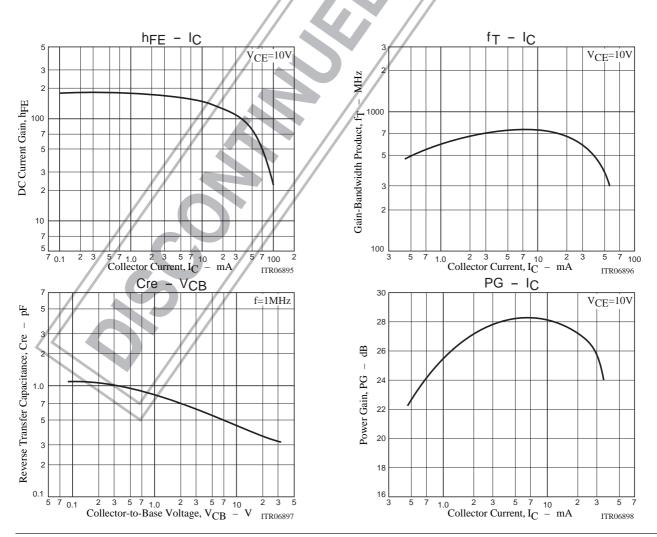
SANYO Electric Co., Ltd. Semiconductor Company TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN Continued from preceding page.

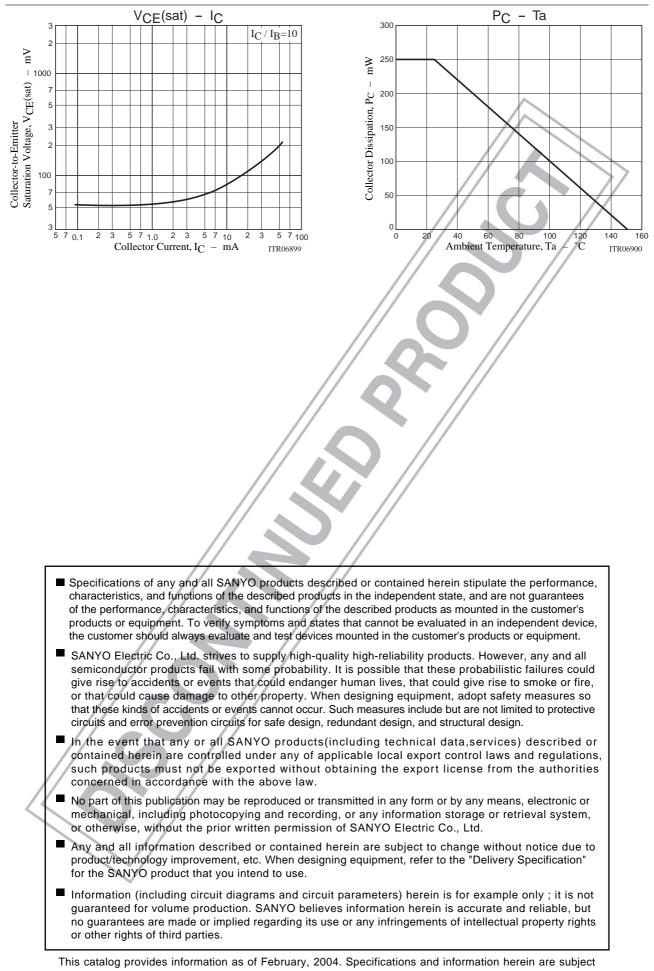
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector-to-Emitter Saturation Voltage	VCE(sat)	I _C =10mA, I _B =1mA			0.2	V
Base-to-Collector Time Constant	rbb'Cc	V _{CE} =10V, I _C =5mA, f=31.9MHz			23	ps
Power Gain	PG	V _{CE} =10V, I _C =10mA, f=100MHz		28		dB

PG Test Circuit



- L1 : 1mmø plated wire, 10mmø 5T, pitch 15mm, tap : 2T from base side.
- L2 : 1mmø plated wire, 10mmø 7T, pitch 10mm, tap : from VC side.
- L3 : 1mmø enamel wire, 10mmø 3T, pitch 10mm





to change without notice.